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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I ² C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	47
Program Memory Size	48KB (48K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 12x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	52-LQFP
Supplier Device Package	52-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21357cdfp-30

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Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

R8C/35C Group 1. Overview

Table 1.4 Pin Name Information by Pin Number (1)

			I/O Pin Functions for Peripheral Modules						
Pin Number	Control Pin	Port	Interrupt	Timer	Serial Interface	SSU	I ² C bus	A/D Converter, D/A Converter, Comparator B	
1		P5_6		(TRAO)					
2		P3_2	(INT1/INT2)	(TRAIO)					
3		P3_0		(TRAO)					
4		P4_2						VREF	
5	MODE								
6	(XCIN)	P4_3							
7	(XCOUT)	P4_4							
8	RESET								
9	XOUT	P4_7							
10	VSS/AVSS								
11	XIN	P4_6							
12 13	VCC/AVCC	P3_7		TRAO	(RXD2/SCL2/ TXD2/SDA2)	SSO	SDA		
14		P3_5		(TRCIOD)	(CLK2)	SSCK	SCL		
15		P3_4		(TRCIOC)	(RXD2/SCL2/ TXD2/SDA2)	SSI		IVREF3	
16		P3_3	ĪNT3	(TRCCLK)	(CTS2/RTS2)	SCS		IVCMP3	
17		P2_7		(TRDIOD1)					
18		P2_6		(TRDIOC1)					
19		P2_5		(TRDIOB1)					
20		P2_4		(TRDIOA1)					
21		P2_3		(TRDIOD0)					
22		P2_2		(TRCIOD/ TRDIOB0)					
23		P2_1		(TRCIOC/ TRDIOC0)					
24		P2_0	(INT1)	(TRCIOB/ TRDIOA0/ TRDCLK)					
25		P3_6	(INT1)						
26		P3_1		(TRBO)					
27		P6_7	(INT3)	(TRCIOD)					
28		P6_6	INT2	(TRCIOC)	(TXD2/SDA2)				
29		P6_5	INT4	(TRCIOB)	(CLK1/CLK2)				
30		P4_5	ĪNT0		(RXD2/SCL2)			ADTRG	
31		P1_7	ĪNT1	(TRAIO)				IVCMP1	
32		P1_6			(CLK0)			IVREF1	
33		P1_5	(INT1)	(TRAIO)	(RXD0)				
34		P1_4	·	(TRCCLK)	(TXD0)				
35		P1_3	KI3	TRBO (/TRCIOC)				AN11	

Note:

1. Can be assigned to the pin in parentheses by a program.

R8C/35C Group 3. Memory

3. Memory

3.1 R8C/35C Group

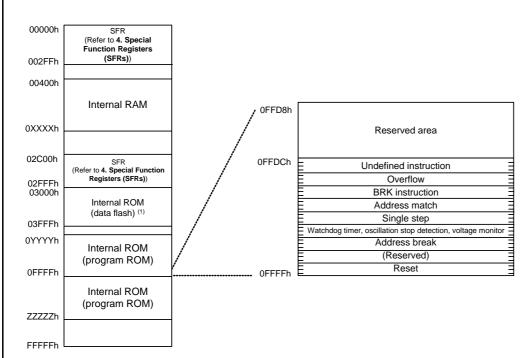
Figure 3.1 is a Memory Map of R8C/35C Group. The R8C/35C Group has a 1-Mbyte address space from addresses 00000h to FFFFh. The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 32-Kbyte internal ROM area is allocated addresses 08000h to 0FFFFh.

The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. The starting address of each interrupt routine is stored here.

The internal ROM (data flash) is allocated addresses 03000h to 03FFFh.

The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 2.5-Kbyte internal RAM area is allocated addresses 00400h to 00DFFh. The internal RAM is used not only for data storage but also as a stack area when a subroutine is called or when an interrupt request is acknowledged.

Special function registers (SFRs) are allocated addresses 00000h to 002FFh and 02C00h to 02FFFh. Peripheral function control registers are allocated here. All unallocated spaces within the SFRs are reserved and cannot be accessed by users.



Notes:

- 1. Data flash indicates block A (1 Kbyte), block B (1 Kbyte), block C (1 Kbyte), and block D (1 Kbyte).
- 2. The blank areas are reserved and cannot be accessed by users.

Deat Neverlee	Internal ROM			Internal RAM		
Part Number	Size	Address 0YYYYh	Address ZZZZZh	Size	Address 0XXXXh	
R5F21354CNFP, R5F21354CDFP	16 Kbytes	0C000h	_	1.5 Kbytes	009FFh	
R5F21355CNFP, R5F21355CDFP	24 Kbytes	0A000h	_	2 Kbytes	00BFFh	
R5F21356CNFP, R5F21356CDFP	32 Kbytes	08000h	_	2.5 Kbytes	00DFFh	
R5F21357CNFP, R5F21357CDFP	48 Kbytes	04000h	_	4 Kbytes	013FFh	
R5F21358CNFP, R5F21358CDFP	64 Kbytes	04000h	13FFFh	6 Kbytes	01BFFh	
R5F2135ACNFP, R5F2135ACDFP	96 Kbytes	04000h	1BFFFh	8 Kbytes	023FFh	
R5F2135CCNFP, R5F2135CCDFP	128 Kbytes	04000h	23FFFh	10 Kbytes	02BFFh	

Figure 3.1 Memory Map of R8C/35C Group

SFR Information (2) (1) Table 4.2

Address	Register	Symbol	After Reset
003Ah	Voltage Monitor 2 Circuit Control Register	VW2C	10000010b
003Bh			
003Ch			
003Dh			
003Eh			
003Fh			
0040h			
0041h	Flash Memory Ready Interrupt Control Register	FMRDYIC	XXXXX000b
0042h			
0043h			
0044h			
0045h			
0046h	INT4 Interrupt Control Register	INT4IC	XX00X000b
0047h	Timer RC Interrupt Control Register	TRCIC	XXXXXX000b
004711 0048h	Timer RD0 Interrupt Control Register	TRD0IC	XXXXX000b
		TRDIIC	
0049h	Timer RD1 Interrupt Control Register		XXXXX000b
004Ah	Timer RE Interrupt Control Register	TREIC	XXXXX000b
004Bh	UART2 Transmit Interrupt Control Register	S2TIC	XXXXX000b
004Ch	UART2 Receive Interrupt Control Register	S2RIC	XXXXX000b
004Dh	Key Input Interrupt Control Register	KUPIC	XXXXX000b
004Eh	A/D Conversion Interrupt Control Register	ADIC	XXXXX000b
004Fh	SSU Interrupt Control Register / IIC bus Interrupt Control Register (2)	SSUIC / IICIC	XXXXX000b
0050h			
0051h	UART0 Transmit Interrupt Control Register	SOTIC	XXXXX000b
0051h	UARTO Receive Interrupt Control Register	SORIC	XXXXX000b XXXXXX000b
0052h	UART1 Transmit Interrupt Control Register	S1TIC	XXXXX000b
	HARTA Receive Interrupt Control Register		
0054h	UART1 Receive Interrupt Control Register	S1RIC	XXXXX000b
0055h	INT2 Interrupt Control Register	INT2IC	XX00X000b
0056h	Timer RA Interrupt Control Register	TRAIC	XXXXX000b
0057h			
0058h	Timer RB Interrupt Control Register	TRBIC	XXXXX000b
0059h	INT1 Interrupt Control Register	INT1IC	XX00X000b
005Ah	INT3 Interrupt Control Register	INT3IC	XX00X000b
005Bh			
005Ch			
005Dh	INT0 Interrupt Control Register	INTOIC	XX00X000b
005Eh	UART2 Bus Collision Detection Interrupt Control Register	U2BCNIC	XXXXX000b
005Fh	Office Data Complete Detection Interrupt Control Register	02501110	70000000
0060h			
0061h			
0062h			
0063h			
0064h			
0065h			
0066h			
0067h			
0068h			
0069h			
006Ah			
006Bh			
006Ch			
006Ch			
006Eh			
006Fh			
0070h			
0071h			
0072h	Voltage Monitor 1 Interrupt Control Register	VCMP1IC	XXXXX000b
0073h	Voltage Monitor 2 Interrupt Control Register	VCMP2IC	XXXXX000b
0074h			
0075h			
0076h			
0077h			
0077h			
0078h			
007Ah			
007Bh			
007Ch			
007Dh			
007Eh			
		İ	

X: Undefined

Notes: 1. 2.

- The blank areas are reserved and cannot be accessed by users. Selectable by the IICSEL bit in the SSUIICSR register.

SFR Information (4) (1) Table 4.4

Address	Register	Symbol	After Reset
00C0h	A/D Register 0	AD0	XXh
00C1h			000000XXb
00C2h	A/D Register 1	AD1	XXh
00C3h			000000XXb
00C4h	A/D Register 2	AD2	XXh
00C5h			000000XXb
00C6h	A/D Register 3	AD3	XXh
00C7h	1		000000XXb
00C8h	A/D Register 4	AD4	XXh
00C9h			000000XXb
00CAh	A/D Register 5	AD5	XXh
00CBh	_ / V J (Nog. oto)	7.20	000000XXb
00CCh	A/D Register 6	AD6	XXh
00CDh	_ / V - Nog.oto. 0	7.20	000000XXb
00CEh	A/D Register 7	AD7	XXh
00CFh	- 7 V Cognotor /	1.5.	000000XXb
00D0h			0000007070
00D0h			
00D111			
00D2H			
00D3H	A/D Mode Register	ADMOD	00h
00D4H	A/D Input Select Register	ADMOD	11000000b
00D5H		ADCON0	00h
	A/D Control Register 0		
00D7h	A/D Control Register 1	ADCON1	00h
00D8h	D/A0 Register	DA0	00h
00D9h	D/A1 Register	DA1	00h
00DAh			
00DBh			
00DCh	D/A Control Register	DACON	00h
00DDh			
00DEh			
00DFh			
00E0h	Port P0 Register	P0	XXh
00E1h	Port P1 Register	P1	XXh
00E2h	Port P0 Direction Register	PD0	00h
00E3h	Port P1 Direction Register	PD1	00h
00E4h	Port P2 Register	P2	XXh
00E5h	Port P3 Register	P3	XXh
00E6h	Port P2 Direction Register	PD2	00h
00E7h	Port P3 Direction Register	PD3	00h
00E8h	Port P4 Register	P4	XXh
00E9h	Port P5 Register	P5	XXh
00EAh	Port P4 Direction Register	PD4	00h
00EBh	Port P5 Direction Register	PD5	00h
00ECh	Port P6 Register	P6	XXh
00EDh			
00EEh	Port P6 Direction Register	PD6	00h
00EFh	, , , , , , , , , , , , , , , , , , ,	-	
00F0h			
00F1h			
00F2h		+	
00F3h		+	
00F4h			
00F5h			
00F6h			
00F7h			
00F8h			
00F9h			
00F9h			
00FBh			
00FCh			
00FDh			
00FEh			
00FFh			
Undofined			

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

SFR Information (8) (1) Table 4.8

Address	Register	Symbol	After Reset
01C0h	Address Match Interrupt Register 0	RMAD0	XXh
01C1h			XXh
01C2h			0000XXXXb
01C3h	Address Match Interrupt Enable Register 0	AIER0	00h
01C4h	Address Match Interrupt Register 1	RMAD1	XXh
01C5h			XXh
01C6h			0000XXXXb
01C7h	Address Match Interrupt Enable Register 1	AIER1	00h
01C8h			
01C9h			
01CAh			
01CBh			
01CCh			
01CDh			
01CEh			
01CFh			
01D0h			
01D1h			
01D2h			
01D3h	 	 	
01D4h	+		
01D5h	 	 	
01D6h			
01D7h			
01D8h			
01D9h			
01DAh	+		
01DRh			
01DCh	+		
01DDh			
01DBh			
01DEII			
01E0h	Pull-Up Control Register 0	PUR0	00b
01E0II	Pull-Up Control Register 1		00h
01E1fi	Pull-Op Control Register 1	PUR1	00h
01E3h			
01E4h			
01E5h			
01E6h			
01E7h			
01E8h			
01E9h			
01EAh			
01EBh			
01ECh			
01EDh			
01EEh			
01EFh			
01F0h	Port P1 Drive Capacity Control Register	P1DRR	00h
01F1h	Port P2 Drive Capacity Control Register	P2DRR	00h
01F2h	Drive Capacity Control Register 0	DRR0	00h
01F3h	Drive Capacity Control Register 1	DRR1	00h
01F4h			
01F5h	Input Threshold Control Register 0	VLT0	00h
01F6h	Input Threshold Control Register 1	VLT1	00h
01F7h			
01F8h	Comparator B Control Register 0	INTCMP	00h
011 011	† · · · · · · · · · · · · · · · · · · ·		
01F9h		INTEN	00h
01F9h	External Input Enable Register 0		
01F9h 01FAh	External Input Enable Register 0 External Input Enable Register 1		00h
01F9h 01FAh 01FBh	External Input Enable Register 1	INTEN1	00h
01F9h 01FAh 01FBh 01FCh	External Input Enable Register 1 INT Input Filter Select Register 0	INTEN1 INTF	00h 00h
01F9h 01FAh 01FBh	External Input Enable Register 1	INTEN1	00h

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

SFR Information (10) ⁽¹⁾ **Table 4.10**

Address	Register	Symbol	After Reset
2C70h	DTC Control Data 6	DTCD6	XXh
2C71h	DTO CONTO Data o	B1680	XXh
2C72h	-		XXh
2C73h	-		XXh
2C73h	-		XXh
2C7411	-		XXh
2C76h	-		XXh
	4		XXh
2C77h 2C78h	DTC Control Data 7	DTCD7	XXh
	DTC Control Data 7	ысы	
2C79h	4		XXh
2C7Ah			XXh
2C7Bh			XXh
2C7Ch			XXh
2C7Dh			XXh
2C7Eh			XXh
2C7Fh			XXh
2C80h	DTC Control Data 8	DTCD8	XXh
2C81h			XXh
2C82h			XXh
2C83h			XXh
2C84h			XXh
2C85h			XXh
2C86h			XXh
2C87h			XXh
2C88h	DTC Control Data 9	DTCD9	XXh
2C89h			XXh
2C8Ah			XXh
2C8Bh			XXh
2C8Ch			XXh
2C8Dh			XXh
2C8Eh			XXh
2C8Fh			XXh
2C90h	DTC Control Data 10	DTCD10	XXh
2C91h			XXh
2C92h	1		XXh
2C93h	†		XXh
2C94h	†		XXh
2C95h	†		XXh
2C96h	1		XXh
2C97h	-		XXh
2C98h	DTC Control Data 11	DTCD11	XXh
2C99h	DTC Control Bata 11	BIGBII	XXh
2C9Ah	-		XXh
2C9An	-		XXh
2C9Bn	-		XXh
2C9Ch	-		XXh
	-		XXh
2C9Eh	4		
2C9Fh	DTC Control Data 12	DTCD42	XXh
2CA0h	DTC Control Data 12	DTCD12	XXh
2CA1h	-		XXh
2CA2h			XXh
2CA3h			XXh
2CA4h			XXh
2CA5h			XXh
2CA6h			XXh
2CA7h			XXh
2CA8h	DTC Control Data 13	DTCD13	XXh
2CA9h			XXh
2CAAh	1		XXh
2CABh	1		XXh
2CACh	1		XXh
2CADh	1		XXh
2CAEh	1		XXh
2CAFh	1		XXh
Y: Undefined	1		1,3731

X: Undefined
Note:

1. The blank areas are reserved and cannot be accessed by users.

SFR Information (11) ⁽¹⁾ **Table 4.11**

14510 4.1	or it information (11)		
Address	Register	Symbol	After Reset
2CB0h	DTC Control Data 14	DTCD14	XXh
2CB1h			XXh
2CB2h			XXh
2CB3h]		XXh
2CB4h			XXh
2CB5h	1		XXh
2CB6h			XXh
2CB7h	†		XXh
2CB8h	DTC Control Data 15	DTCD15	XXh
2CB9h	B 10 Control Bata 10	B10B10	XXh
2CBAh	-		XXh
2CBBh	-		XXh
2CBCh			XXh
2CBDh			XXh
2CBEh			XXh
2CBFh			XXh
2CC0h	DTC Control Data 16	DTCD16	XXh
2CC1h			XXh
2CC2h]		XXh
2CC3h			XXh
2CC4h	1		XXh
2CC5h	1		XXh
2CC6h	1		XXh
2CC7h	-		XXh
2CC8h	DTC Control Data 17	DTCD17	XXh
2CC9h	Die control data 17	БТОВТ	XXh
2CCAh	4		XXh
2CCBh			XXh
2CCCh			XXh
2CCDh			XXh
2CCEh			XXh
2CCFh			XXh
2CD0h	DTC Control Data 18	DTCD18	XXh
2CD1h			XXh
2CD2h]		XXh
2CD3h			XXh
2CD4h	1		XXh
2CD5h			XXh
2CD6h	†		XXh
2CD7h	-		XXh
2CD8h	DTC Control Data 19	DTCD19	XXh
2CD9h	Die Control Data 19	БТОБТ9	XXh
	4		
2CDAh	4		XXh
2CDBh	-		XXh
2CDCh	-		XXh
2CDDh			XXh
2CDEh			XXh
2CDFh			XXh
2CE0h	DTC Control Data 20	DTCD20	XXh
2CE1h			XXh
2CE2h			XXh
2CE3h			XXh
2CE4h	1		XXh
2CE5h	1		XXh
2CE6h	1		XXh
2CE7h	1		XXh
2CE8h	DTC Control Data 21	DTCD21	XXh
2CE9h	D 10 Oomiloi Dala 21	D10021	XXh
2CE9fi 2CEAh	4		
	4		XXh
2CEBh	-		XXh
2CECh			XXh
2CEDh			XXh
2CEEh			XXh
2CEFh			XXh
V: Undofined			

X: Undefined
Note:

1. The blank areas are reserved and cannot be accessed by users.

R8C/35C Group 5. Electrical Characteristics

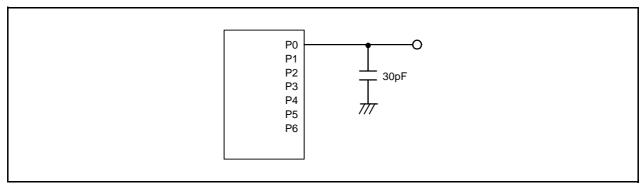


Figure 5.1 Ports P0 to P6 Timing Measurement Circuit

Table 5.7 Flash Memory (Data flash Block A to Block D) Electrical Characteristics

Symbol	Parameter	Conditions		Stand	ard	Unit
Symbol	Farameter	Conditions	Min.	Тур.	Max.	Offic
_	Program/erase endurance (2)		10,000 (3)	-	-	times
_	Byte program time (program/erase endurance ≤ 1,000 times)		_	160	1,500	μS
-	Byte program time (program/erase endurance > 1,000 times)		-	300	1,500	μS
_	Block erase time (program/erase endurance ≤ 1,000 times)		-	0.2	1	S
-	Block erase time (program/erase endurance > 1,000 times)		_	0.3	1	S
td(SR-SUS)	Time delay from suspend request until suspend		-	-	5+CPU clock × 3 cycles	ms
_	Interval from erase start/restart until following suspend request		0	=	-	μS
_	Time from suspend until erase restart		_	-	30+CPU clock × 1 cycle	μS
td(CMDRST- READY)	Time from when command is forcibly terminated until reading is enabled		-	-	30+CPU clock × 1 cycle	μS
-	Program, erase voltage		2.7	-	5.5	V
-	Read voltage		1.8	-	5.5	V
=	Program, erase temperature		-20 ⁽⁷⁾	-	85	°C
=	Data hold time (8)	Ambient temperature = 55 °C	20	-	=	year

- 1. Vcc = 2.7 to 5.5 V and Topr = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
- 2. Definition of programming/erasure endurance
 - The programming and erasure endurance is defined on a per-block basis.
 - If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
 - However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
- 3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
- 4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A to D can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
- 5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
- 6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
- 7. –40°C for D version.
- 8. The data hold time includes time that the power supply is off or the clock is not supplied.

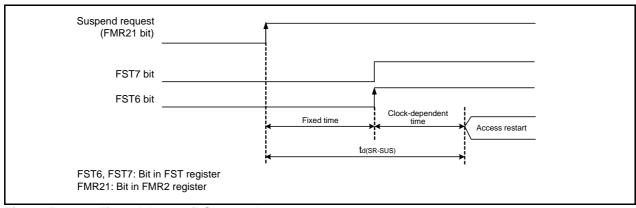


Figure 5.2 Time delay until Suspend

Table 5.8 Voltage Detection 0 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
Syllibol	Farameter	Condition	Min.	Тур.	Max.	Offic
Vdet0	Voltage detection level Vdet0_0 (2)		1.80	1.90	2.05	V
	Voltage detection level Vdet0_1 (2)		2.15	2.35	2.50	V
	Voltage detection level Vdet0_2 (2)		2.70	2.85	3.05	V
	Voltage detection level Vdet0_3 (2)		3.55	3.80	4.05	V
_	Voltage detection 0 circuit response time (4)	At the falling of Vcc from 5 V to (Vdet0_0 – 0.1) V	-	6	150	μS
=	Voltage detection circuit self power consumption	VCA25 = 1, Vcc = 5.0 V	-	1.5	-	μΑ
td(E-A)	Waiting time until voltage detection circuit operation starts (3)		-	-	100	μS

Notes:

- 1. The measurement condition is Vcc = 1.8 V to 5.5 V and Topr = -20 to 85°C (N version) / -40 to 85°C (D version).
- 2. Select the voltage detection level with bits VDSEL0 and VDSEL1 in the OFS register.
- 3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA25 bit in the VCA2 register to 0.
- 4. Time until the voltage monitor 0 reset is generated after the voltage passes Vdeto.

Table 5.9 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition		Standard	ł	Unit
Symbol	Falameter	Condition	Min.	Тур.	Max.	Offic
Vdet1	Voltage detection level Vdet1_0 (2)	At the falling of Vcc	2.00	2.20	2.40	V
	Voltage detection level Vdet1_1 (2)	At the falling of Vcc	2.15	2.35	2.55	V
	Voltage detection level Vdet1_2 (2)	At the falling of Vcc	2.30	2.50	2.70	V
	Voltage detection level Vdet1_3 (2)	At the falling of Vcc	2.45	2.65	2.85	V
	Voltage detection level Vdet1_4 (2)	At the falling of Vcc	2.60	2.80	3.00	V
	Voltage detection level Vdet1_5 (2)	At the falling of Vcc	2.75	2.95	3.15	V
	Voltage detection level Vdet1_6 (2)	At the falling of Vcc	2.85	3.10	3.40	V
	Voltage detection level Vdet1_7 (2)	At the falling of Vcc	3.00	3.25	3.55	V
	Voltage detection level Vdet1_8 (2)	At the falling of Vcc	3.15	3.40	3.70	V
	Voltage detection level Vdet1_9 (2)	At the falling of Vcc	3.30	3.55	3.85	V
	Voltage detection level Vdet1_A (2)	At the falling of Vcc	3.45	3.70	4.00	V
	Voltage detection level Vdet1_B (2)	At the falling of Vcc	3.60	3.85	4.15	V
	Voltage detection level Vdet1_C (2)	At the falling of Vcc	3.75	4.00	4.30	V
	Voltage detection level Vdet1_D (2)	At the falling of Vcc	3.90	4.15	4.45	V
	Voltage detection level Vdet1_E (2)	At the falling of Vcc	4.05	4.30	4.60	V
	Voltage detection level Vdet1_F (2)	At the falling of Vcc	4.20	4.45	4.75	V
_	Hysteresis width at the rising of Vcc in voltage detection 1 circuit	Vdet1_0 to Vdet1_5 selected	-	0.07	-	V
		Vdet1_6 to Vdet1_F selected	-	0.10	-	V
_	Voltage detection 1 circuit response time (3)	At the falling of Vcc from 5 V to (Vdet1_0 - 0.1) V	-	60	150	μS
_	Voltage detection circuit self power consumption	VCA26 = 1, Vcc = 5.0 V	_	1.7	_	μΑ
td(E-A)	Waiting time until voltage detection circuit operation starts (4)		-	-	100	μS

- 1. The measurement condition is Vcc = 1.8 V to 5.5 V and Topr = -20 to $85^{\circ}C$ (N version) / -40 to $85^{\circ}C$ (D version).
- 2. Select the voltage detection level with bits VD1S0 to VD1S3 in the VD1LS register.
- ${\it 3.} \quad {\it Time until the voltage monitor 1 interrupt request is generated after the voltage passes V_{det1}.}$
- 4. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.



R8C/35C Group 5. Electrical Characteristics

Symbol	Parameter	Condition		Unit		
	Parameter	Condition	Min.	Тур.	Max.	Unit
Vdet2	Voltage detection level Vdet2_0	At the falling of Vcc	3.70	4.00	4.30	V
_	Hysteresis width at the rising of Vcc in voltage detection 2 circuit		-	0.10	-	V
_	Voltage detection 2 circuit response time (2)	At the falling of Vcc from 5 V to (Vdet2_0 - 0.1) V	-	20	150	μS
_	Voltage detection circuit self power consumption	VCA27 = 1, Vcc = 5.0 V	_	1.7	_	μА
td(E-A)	Waiting time until voltage detection circuit operation starts ⁽³⁾		-	_	100	μS

Notes:

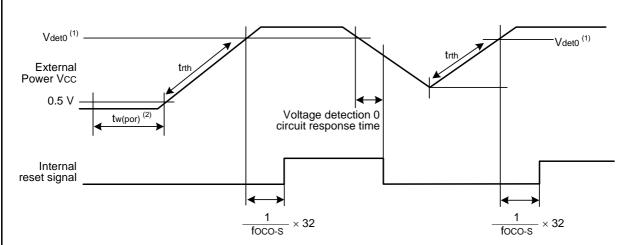
- 1. The measurement condition is Vcc = 1.8 V to 5.5 V and $T_{opr} = -20$ to $85^{\circ}C$ (N version) / -40 to $85^{\circ}C$ (D version).
- 2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes Vdet2.
- 3. Necessary time until the voltage detection circuit operates after setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.

Table 5.11 Power-on Reset Circuit (2)

Symbol	Parameter	Condition		Unit		
Symbol	Falametei	Condition	Min.	Тур.	Max.	Offic
trth	External power Vcc rise gradient	(1)	0	_	50,000	mV/msec

Notes:

- 1. The measurement condition is Topr = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
- 2. To use the power-on reset function, enable voltage monitor 0 reset by setting the LVDAS bit in the OFS register to 0.



- Vdeto indicates the voltage detection level of the voltage detection 0 circuit. Refer to 6. Voltage Detection Circuit of User's Manual: Hardware (REJ09B0567) for details.
- 2. tw(por) indicates the duration the external power Vcc must be held below the valid voltage (0.5 V) to enable a power-on reset. When turning on the power after it falls with voltage monitor 0 reset disabled, maintain tw(por) for 1 ms or more.

Figure 5.3 Power-on Reset Circuit Electrical Characteristics

Table 5.16 Timing Requirements of I²C bus Interface (1)

Symbol	Parameter	Condition	St	Unit		
	Parameter	Condition	Min.	Тур.	Max.	Onit
tscl	SCL input cycle time		12tcyc + 600 (2)	-	-	ns
tsclh	SCL input "H" width		3tcyc + 300 (2)	=	-	ns
tscll	SCL input "L" width		5tcyc + 500 (2)	=	=	ns
tsf	SCL, SDA input fall time		=	=	300	ns
tsp	SCL, SDA input spike pulse rejection time		-	=	1tcyc (2)	ns
tBUF	SDA input bus-free time		5tcyc (2)	=	=	ns
tstah	Start condition input hold time		3tcyc (2)	=	-	ns
tstas	Retransmit start condition input setup time		3tcyc (2)	=	=	ns
tstop	Stop condition input setup time		3tcyc (2)	=	=	ns
tsdas	Data input setup time 1tcyc + 40 (2) -		-	ns		
tsdah	Data input hold time		10	-	-	ns

- 1. Vcc = 1.8 to 5.5 V, Vss = 0 V and $T_{opr} = -20$ to $85^{\circ}C$ (N version) / -40 to $85^{\circ}C$ (D version), unless otherwise specified.
- 2. 1tcyc = 1/f1(s)

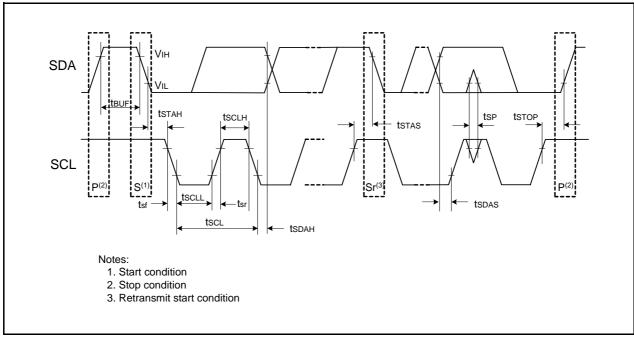


Figure 5.7 I/O Timing of I²C bus Interface

Timing Requirements

(Unless Otherwise Specified: Vcc = 5 V, Vss = 0 V at Topr = 25°C)

Table 5.19 External Clock Input (XOUT, XCIN)

Symbol	Parameter		Standard		
Symbol			Max.	Unit	
tc(XOUT)	XOUT input cycle time	50	-	ns	
twh(xout)	XOUT input "H" width	24	-	ns	
tWL(XOUT)	XOUT input "L" width	24	-	ns	
tc(XCIN)	XCIN input cycle time	14	-	μS	
twh(xcin)	XCIN input "H" width	7	=	μS	
tWL(XCIN)	XCIN input "L" width	7	_	μS	

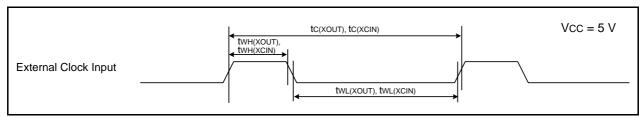


Figure 5.8 External Clock Input Timing Diagram when VCC = 5 V

Table 5.20 TRAIO Input

Symbol	Parameter		Standard		
			Max.	Unit	
tc(TRAIO)	TRAIO input cycle time	100	=	ns	
twh(traio)	TRAIO input "H" width		=	ns	
twl(traio)	TRAIO input "L" width	40	_	ns	

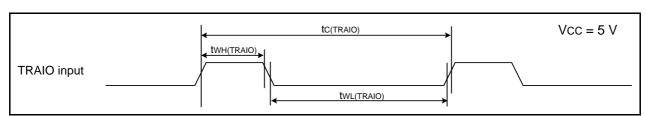


Figure 5.9 TRAIO Input Timing Diagram when Vcc = 5 V

R8C/35C Group 5. Electrical Characteristics

Electrical Characteristics (4) [2.7 V \leq Vcc < 3.3 V] **Table 5.24** (Topr = -20 to 85° C (N version) / -40 to 85° C (D version), unless otherwise specified.)

Symbol	Parameter		Condition		Standard	d Max.	Unit
Icc	Power supply current	High-speed	XIN = 10 MHz (square wave)	Min.	Typ. 3.5	10 10	mA
	(Vcc = 2.7 to 3.3 V) Single-chip mode,	clock mode	High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	_	3.5	10	ША
	output pins are open, other pins are Vss		XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	_	1.5	7.5	mA
		High-speed on-chip oscillator	XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	_	7.0	15	mA
		mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	_	3.0	=	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division	-	4.0	=	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	_	1.5	=	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16 MSTIIC = MSTTRD = MSTTRC = 1	-	1	-	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	=	90	390	μА
Low-sp	Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division, FMR27 = 1, VCA20 = 0	-	80	400	μА	
		XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division, Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0	_	40	_	μА	
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	_	15	90	μА
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	_	4	80	μА
		XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	_	3.5	_	μА	
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	=	2.0	5.0	μА
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1	-	5.0 ⁽¹⁾	_	μА
			Peripheral clock off VCA27 = VCA26 = VCA25 = 0				

- Value when the program ROM capacity of the product is 16 Kbytes to 32 Kbytes.
 Value when the program ROM capacity of the product is 48 Kbytes to 128 Kbytes.

Table	5 27	Serial	Interface

Symbol	Parameter		Standard		
	Faidilletei	Min.	Max.	Unit	
tc(CK)	CLKi input cycle time	300	-	ns	
tW(CKH)	CLKi input "H" width	150	-	ns	
tW(CKL)	CLKi Input "L" width	150	-	ns	
td(C-Q)	TXDi output delay time	-	80	ns	
th(C-Q)	TXDi hold time		-	ns	
tsu(D-C)	RXDi input setup time 70			ns	
th(C-D)	RXDi input hold time	-	ns		

i = 0 to 2

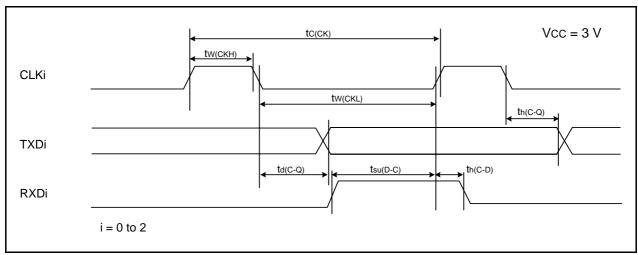


Figure 5.14 Serial Interface Timing Diagram when Vcc = 3 V

Table 5.28 External Interrupt INTi (i = 0 to 4) Input, Key Input Interrupt Kli (i = 0 to 3)

Symbol	Parameter		Standard		
Symbol			Max.	Unit	
tW(INH)	ĪNTi input "H" width, Kli input "H" width	380 (1)	-	ns	
tW(INL)	NTi input "L" width, Kli input "L" width				

- 1. When selecting the digital filter by the INTi input filter select bit, use an INTi input HIGH width of either (1/digital filter clock frequency x 3) or the minimum value of standard, whichever is greater.
- 2. When selecting the digital filter by the $\overline{\text{INTi}}$ input filter select bit, use an $\overline{\text{INTi}}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

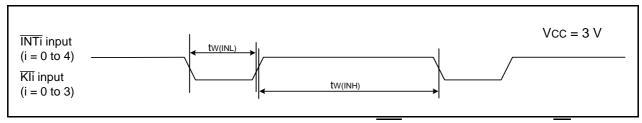


Figure 5.15 Input Timing Diagram for External Interrupt INTi and Key Input Interrupt Kli when Vcc = 3 V

Table 5.29 Electrical Characteristics (5) [1.8 $V \le Vcc < 2.7 V$]

Symbol	Por	ameter	Condition	Condition		Standard		
Symbol	Fai	ametei	Condition		Min.	Тур.	Max.	Unit
Vон	Output "H" voltage	Other than XOUT	Drive capacity High	Iон = −2 mA	Vcc - 0.5	1	Vcc	V
			Drive capacity Low	Iон = −1 mA	Vcc - 0.5	-	Vcc	V
		XOUT		$IOH = -200 \mu A$	1.0	-	Vcc	V
Vol	Output "L" voltage	Other than XOUT	Drive capacity High	IoL = 2 mA	-	-	0.5	V
			Drive capacity Low	IoL = 1 mA	-	-	0.5	V
		XOUT		IoL = 200 μA	-	-	0.5	V
VT+-VT-	Hysteresis	INTO, INT1, INT2, INT3, INT4, KIO, KI1, KI2, KI3, TRAIO, TRBO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, TRDIOAO, TRDIOBO, TRDIOCO, TRDIOBO, TRDIOCO, TRDIOBI, TRDIOC1, TRDIOD1, TRCTRG, TRCCLK, ADTRG, RXD0, RXD1, RXD2, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO RESET			0.05	0.20	_	V
lін	Input "H" current	•	VI = 2.2 V, Vcc = 2.2	! V	-	-	4.0	μΑ
lıL	Input "L" current	Input "L" current		/	-	-	-4.0	μΑ
RPULLUP	Pull-up resistance		VI = 0 V, Vcc = 2.2 V	/	70	140	300	kΩ
RfXIN	Feedback resistance	XIN			-	0.3	_	МΩ
RfXCIN	Feedback resistance	XCIN			-	8	-	МΩ
VRAM	RAM hold voltage	•	During stop mode		1.8	=	-	V

^{1.} $1.8 \text{ V} \le \text{Vcc} < 2.7 \text{ V}$ and $\text{Topr} = -20 \text{ to } 85^{\circ}\text{C}$ (N version) / -40 to 85°C (D version), f(XIN) = 5 MHz, unless otherwise specified.

Table 5.30 Electrical Characteristics (6) [1.8 V \leq Vcc < 2.7 V] (Topr = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter		Condition		Standard		
Symbol	raiametei		Condition	Min.	Тур.	Max.	Unit
Icc	Power supply current (Vcc = 1.8 to 2.7 V) Single-chip mode, output pins are open,	High-speed clock mode	XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	=	2.2	=	mA
other pins are Vss		XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	_	0.8	ı	mA	
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 5 MHz Low-speed on-chip oscillator on = 125 kHz No division	-	2.5	10	mA
		mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 5 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	-	1.7	-	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16 MSTIIC = MSTTRD = MSTTRC = 1	-	1	-	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	-	90	300	μА
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division, FMR27 = 1, VCA20 = 0	=	80	350	μА
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division, Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0	_	40		μА
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	_	15	90	μА
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	-	4	80	μА
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	=	3.5	=	μА
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	_	2.0	5	μА
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off	_	5.0 ⁽¹⁾	-	μА

- 1. Value when the program ROM capacity of the product is 16 Kbytes to 32 Kbytes.
- 2. Value when the program ROM capacity of the product is 48 Kbytes to 128 Kbytes.

REVISION HISTORY	R8C/35C Group Datasheet
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Rev.	Date	Description	
		Page	Summary
0.10	Sep. 01, 2009	_	First Edition issued
1.00	Aug. 24, 2010	All	"Preliminary" and "Under development" deleted
		4	Table1.3 revised
		27 to 53	5. Electrical Characteristics added

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General Precautions in the Handling of MPU/MCU Products

The following usage notes are applicable to all MPU/MCU products from Renesas. For detailed usage notes on the products covered by this manual, refer to the relevant sections of the manual. If the descriptions under General Precautions in the Handling of MPU/MCU Products and in the body of the manual differ from each other, the description in the body of the manual takes precedence.

1. Handling of Unused Pins

Handle unused pins in accord with the directions given under Handling of Unused Pins in the manual.

The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible. Unused pins should be handled as described under Handling of Unused Pins in the manual.

2. Processing at Power-on

The state of the product is undefined at the moment when power is supplied.

The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the moment when power is supplied.

In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the moment when power is supplied until the reset process is completed.

In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the moment when power is supplied until the power reaches the level at which resetting has been specified.

3. Prohibition of Access to Reserved Addresses

Access to reserved addresses is prohibited.

 The reserved addresses are provided for the possible future expansion of functions. Do not access these addresses; the correct operation of LSI is not guaranteed if they are accessed.

4. Clock Signals

After applying a reset, only release the reset line after the operating clock signal has become stable. When switching the clock signal during program execution, wait until the target clock signal has stabilized.

— When the clock signal is generated with an external resonator (or from an external oscillator) during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Moreover, when switching to a clock signal produced with an external resonator (or by an external oscillator) while program execution is in progress, wait until the target clock signal is stable.

5. Differences between Products

Before changing from one product to another, i.e. to one with a different part number, confirm that the change will not lead to problems.

— The characteristics of MPU/MCU in the same group but having different part numbers may differ because of the differences in internal memory capacity and layout pattern. When changing to products of different part numbers, implement a system-evaluation test for each of the products.

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